

Clean copy of Pending Claims as filed in Response to Office Action dated June 19, 2002:

1.(Amended) A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of and on a layer, wherein said polysilicon resistor is formed using a doping wherein said doping has a concentration of from $\sim 6 \times 10^{19} \text{ cm}^{-3}$ to $\sim [3.75] 1 \times 10^{20} \text{ cm}^{-3}$ and wherein said polycrystalline silicon resistor has at least a first and second order temperature coefficient, wherein the sign of said first and second order temperature coefficients are opposite each other.

2.(Amended) A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of on a layer, wherein said polysilicon resistor is formed using a doping wherein said doping has a concentration of less than $\sim 3.75 \times 10^{20} \text{ cm}^{-3}$ and wherein said polycrystalline silicon resistor has at least a first and second order temperature coefficient, wherein the sign of said first and second order temperature coefficients are opposite each other.

11.(Amended) A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of on a layer, wherein said polysilicon resistor is formed using a dopng wherein said doping has a concentration of greater than $\sim 6 \times 10^{19} \text{ cm}^{-3}$ and wherein said polycrystalline silicon resistor has at least a first and second order temperature coefficient, wherein the sign of said first and second order temperature coefficients are opposite each other.

12.(Amended) A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of on a layer, wherein said polysilicon resistor is formed using a late implant doping technique and wherein said polycrystalline silicon resistor has at least a first and second order temperature coefficient, wherein the sign of said first and second order temperature coefficients are opposite each other.